

# Low Voltage Standard Rectifier

$$V_{RRM} = 1200 \text{ V}$$

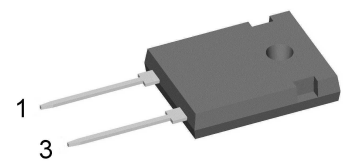
$$I_{FAV} = 60 \text{ A}$$

$$V_F = 1.1 \text{ V}$$

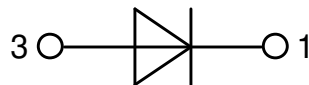
Single Diode

Part number

**DLA60I1200HA**



Backside: cathode



### Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

### Applications:

- Diode for main rectification
- For single and three phase bridge configurations

### Package: TO-247

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

### Disclaimer Notice

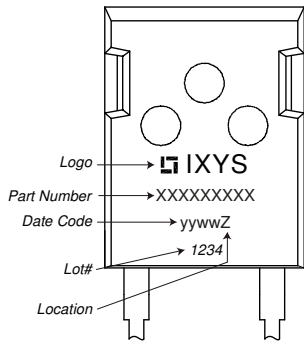
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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM}$	max. non-repetitive reverse blocking voltage					1300	V
$V_{RRM}$	max. repetitive reverse blocking voltage					1200	V
$I_R$	reverse current	$V_R = 1200$ V		$T_{VJ} = 25^\circ\text{C}$		30	$\mu\text{A}$
		$V_R = 1200$ V		$T_{VJ} = 150^\circ\text{C}$		0.3	mA
$V_F$	forward voltage drop	$I_F = 60$ A		$T_{VJ} = 25^\circ\text{C}$		1.19	V
						1.42	V
		$I_F = 120$ A		$T_{VJ} = 150^\circ\text{C}$		1.10	V
						1.41	V
$I_{FAV}$	average forward current	$T_C = 150^\circ\text{C}$	rectangular	$T_{VJ} = 175^\circ\text{C}$		60	A
$V_{FO}$	threshold voltage	} for power loss calculation only		$T_{VJ} = 175^\circ\text{C}$		0.78	V
$r_F$	slope resistance					5.1	m $\Omega$
$R_{thJC}$	thermal resistance junction to case					0.3	K/W
$R_{thCH}$	thermal resistance case to heatsink				0.3		K/W
$P_{tot}$	total power dissipation			$T_C = 25^\circ\text{C}$		500	W
$I_{FSM}$	max. forward surge current	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		850	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		920	A
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		725	A
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		780	A
$I^2t$	value for fusing	$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 45^\circ\text{C}$		3.62	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		3.52	kA <sup>2</sup> s
		$t = 10$ ms; (50 Hz), sine		$T_{VJ} = 150^\circ\text{C}$		2.63	kA <sup>2</sup> s
		$t = 8,3$ ms; (60 Hz), sine		$V_R = 0$ V		2.53	kA <sup>2</sup> s
$C_J$	junction capacitance	$V_R = 400$ V; $f = 1$ MHz		$T_{VJ} = 25^\circ\text{C}$		33	pF



Package TO-247			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
$I_{RMS}$	RMS current	per terminal			70	A
$T_{VJ}$	virtual junction temperature		-55		175	°C
$T_{op}$	operation temperature		-55		150	°C
$T_{stg}$	storage temperature		-55		150	°C
<b>Weight</b>				6		g
$M_D$	mounting torque		0.8		1.2	Nm
$F_C$	mounting force with clip		20		120	N

**Product Marking**



**Part description**

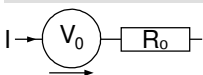
- D = Diode
- L = Low Voltage Standard Rectifier
- A = (up to 1200V)
- 60 = Current Rating [A]
- I = Single Diode
- 1200 = Reverse Voltage [V]
- HA = TO-247AD (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DLA60I1200HA	DLA60I1200HA	Tube	30	508170

**Equivalent Circuits for Simulation**

*\* on die level*

$T_{VJ} = 175^{\circ}C$



**Rectifier**

$V_{0\ max}$	threshold voltage	0.78	V
$R_{0\ max}$	slope resistance *	2.5	mΩ



**Outlines TO-247**



Sym.	Inches		Millimeter	
	min.	max.	min.	max.
A	0.185	0.209	4.70	5.30
A1	0.087	0.102	2.21	2.59
A2	0.059	0.098	1.50	2.49
D	0.819	0.845	20.79	21.45
E	0.610	0.640	15.48	16.24
E2	0.170	0.216	4.31	5.48
e	0.430 BSC		10.92 BSC	
L	0.780	0.800	19.80	20.30
L1	-	0.177	-	4.49
Ø P	0.140	0.144	3.55	3.65
Q	0.212	0.244	5.38	6.19
S	0.242 BSC		6.14 BSC	
b	0.039	0.055	0.99	1.40
b2	0.065	0.094	1.65	2.39
b4	0.102	0.135	2.59	3.43
c	0.015	0.035	0.38	0.89
D1	0.515	-	13.07	-
D2	0.020	0.053	0.51	1.35
E1	0.530	-	13.45	-
Ø P1	-	0.29	-	7.39



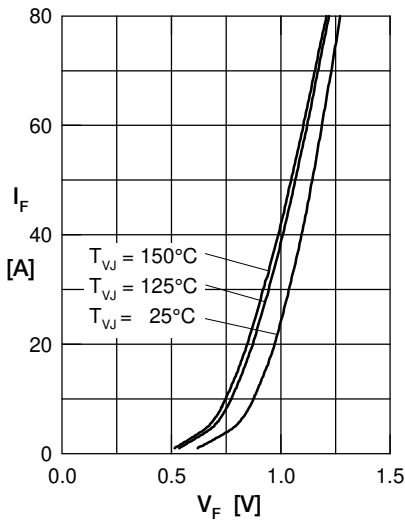
**Rectifier**


Fig. 1 Forward current versus voltage drop per diode

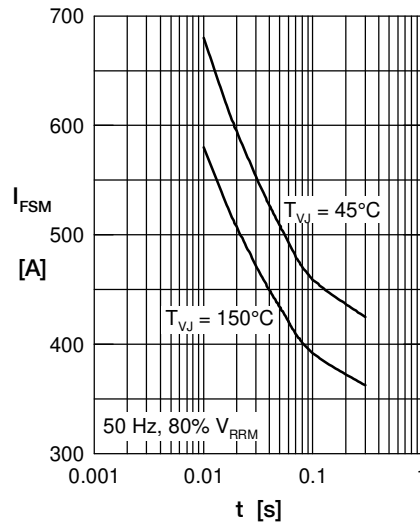


Fig. 2 Surge overload current

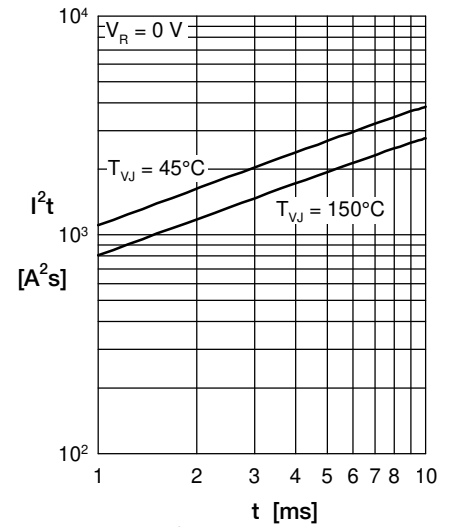
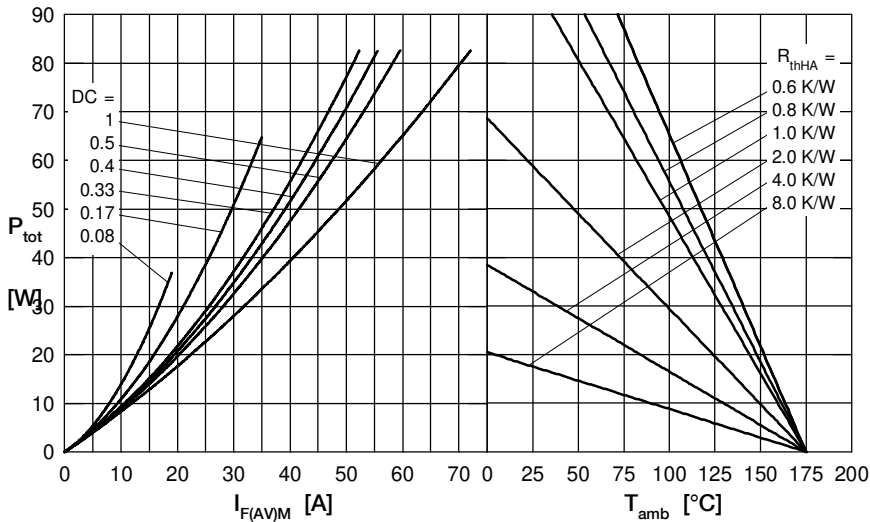

 Fig. 3  $I^2t$  versus time per diode


Fig. 4 Power dissipation vs. direct output current and ambient temperature

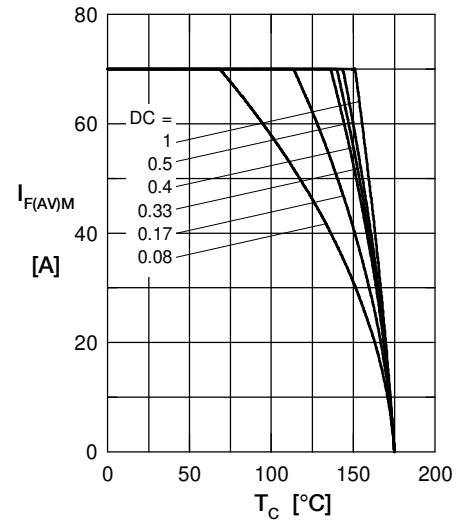


Fig. 5 Max. forward current vs. case temperature

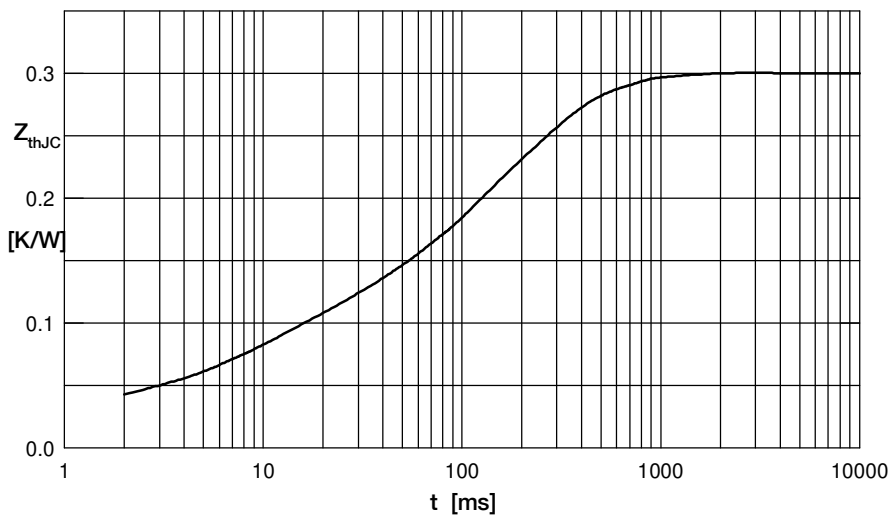


Fig. 6 Transient thermal impedance junction to case

 Constants for  $Z_{thJC}$  calculation:

i	$R_{thi}$ (K/W)	$t_i$ (s)
1	0.044	0.007
2	0.027	0.0001
3	0.029	0.02
4	0.05	0.37
5	0.15	0.15